

MOSFET

OptiMOS™ Small-Signal-Transistor, 100 V

Features

- N-channel
- Enhancement mode
- Logic level (4.5V rated)
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Fully qualified according to JEDEC for Industrial Applications

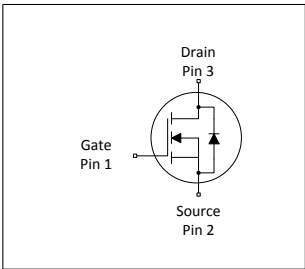


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),max}, V_{GS}=10\text{ V}$	6	Ω
$R_{DS(on),max}, V_{GS}=4.5\text{ V}$	10	Ω
I_D	0.19	A
ESD Sensitivity, JESD22-A114 (HBM)	class 0 (<250V)	



RoHS

Type / Ordering Code	Package	Marking	Related Links
BSS123I	PG-SOT23	Als	-

Table of Contents

Description 1

Maximum ratings 3

Thermal characteristics 3

Electrical characteristics 3

Electrical characteristics diagrams 5

Package Outlines 9

Revision History 10

Trademarks 10

Disclaimer 10

1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	-	-	0.19 0.15	A	$V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$ $V_{GS}=4.5\text{ V}$, $T_A=70\text{ °C}$
Pulsed drain current	$I_{D,pulse}$	-	-	0.77	A	$T_A=25\text{ °C}$
Avalanche energy, single pulse	E_{AS}	-	-	2.0	mJ	$I_D=0.19\text{ A}$, $R_{GS}=25\text{ }\Omega$
Reverse diode dv/dt	dv/dt	-	-	6	kV/ μ s	$I_D=0.19\text{ A}$, $V_{DS}=80\text{ V}$, di/dt=200 A/ μ s, $T_{j,max}=150\text{ °C}$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation ¹⁾	P_{tot}	-	-	0.5	W	$T_A=25\text{ °C}$, $R_{thJA}=250\text{ °C/W}$
Operating and storage temperature	T_j , T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - ambient, minimum footprint ¹⁾	R_{thJA}	-	-	250	K/W	-

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu$ A
Gate threshold voltage	$V_{GS(th)}$	0.8	1.4	1.8	V	$V_{DS}=V_{GS}$, $I_D=13\text{ }\mu$ A
Zero gate voltage drain current	I_{DSS}	-	-	0.01 5	μ A	$V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	-	10	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	2.4 2.7	6 10	Ω	$V_{GS}=10\text{ V}$, $I_D=0.19\text{ A}$ $V_{GS}=4.5\text{ V}$, $I_D=0.15\text{ A}$
Transconductance	g_{fs}	-	0.41	-	S	$ V_{DS} \geq 2 I_D /R_{DS(on)max}$, $I_D=0.15\text{ A}$

¹⁾ Performed on 40mm² FR4 PCB. The traces are 1mm wide, 70 μ m thick and 20mm long; they are present on both sides of the PCB

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	15	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	2.5	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	1.6	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	2.3	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=0.19\text{ A}$, $R_{G,ext}=6\ \Omega$
Rise time	t_r	-	3.2	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=0.19\text{ A}$, $R_{G,ext}=6\ \Omega$
Turn-off delay time	$t_{d(off)}$	-	7.4	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=0.19\text{ A}$, $R_{G,ext}=6\ \Omega$
Fall time	t_f	-	22	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=0.19\text{ A}$, $R_{G,ext}=6\ \Omega$

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	0.04	-	nC	$V_{DD}=50\text{ V}$, $I_D=0.19\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	Q_{gd}	-	0.23	-	nC	$V_{DD}=50\text{ V}$, $I_D=0.19\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total	Q_g	-	0.63	-	nC	$V_{DD}=50\text{ V}$, $I_D=0.19\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	2.5	-	V	$V_{DD}=50\text{ V}$, $I_D=0.19\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	0.19	A	$T_A=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	0.77	A	$T_A=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.86	1.1	V	$V_{GS}=0\text{ V}$, $I_F=0.19\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery time	t_{rr}	-	12	18	ns	$V_R=50\text{ V}$, $I_F=0.19\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}	-	4.3	6.5	nC	$V_R=50\text{ V}$, $I_F=0.19\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$

4 Electrical characteristics diagrams

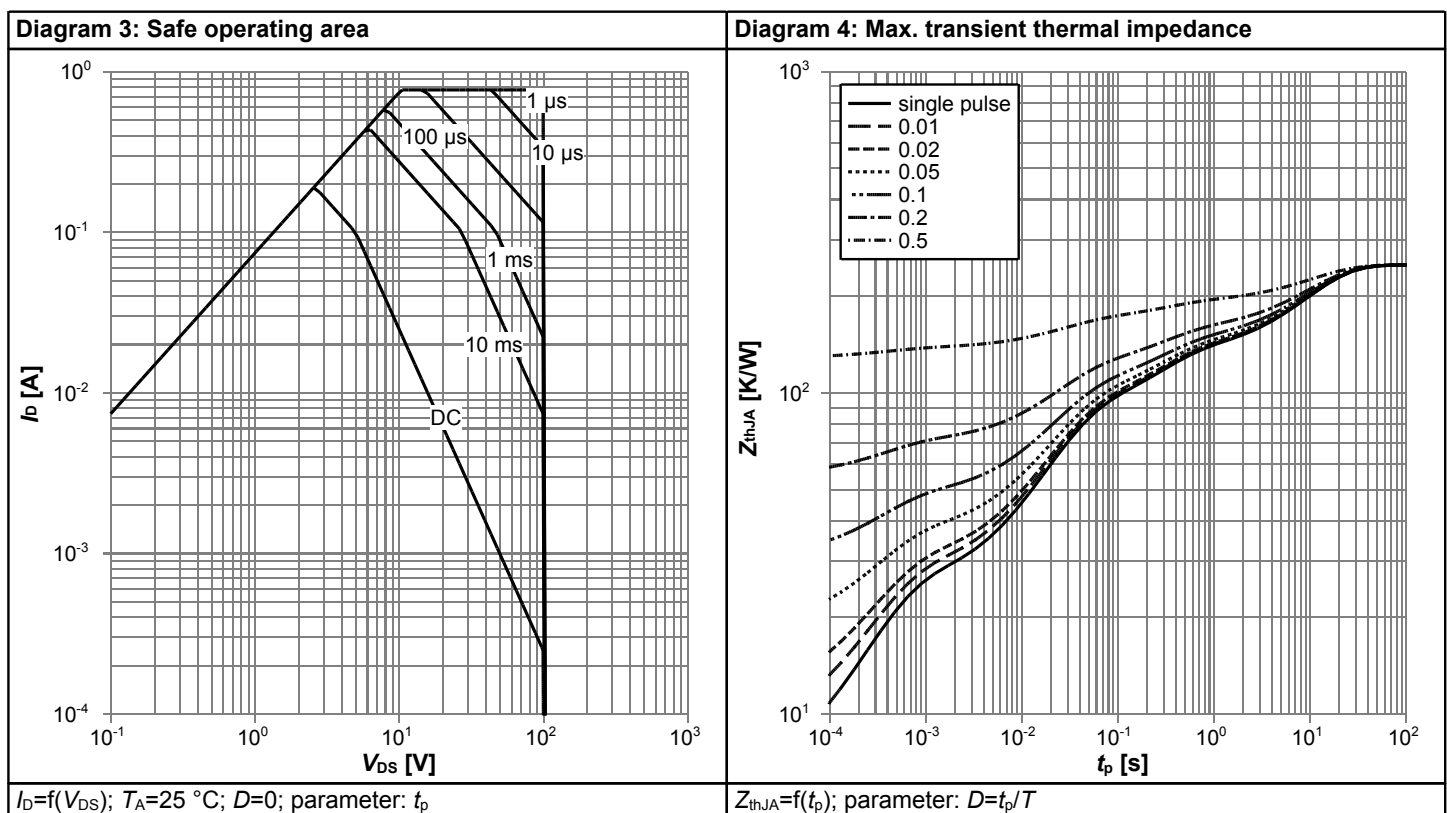
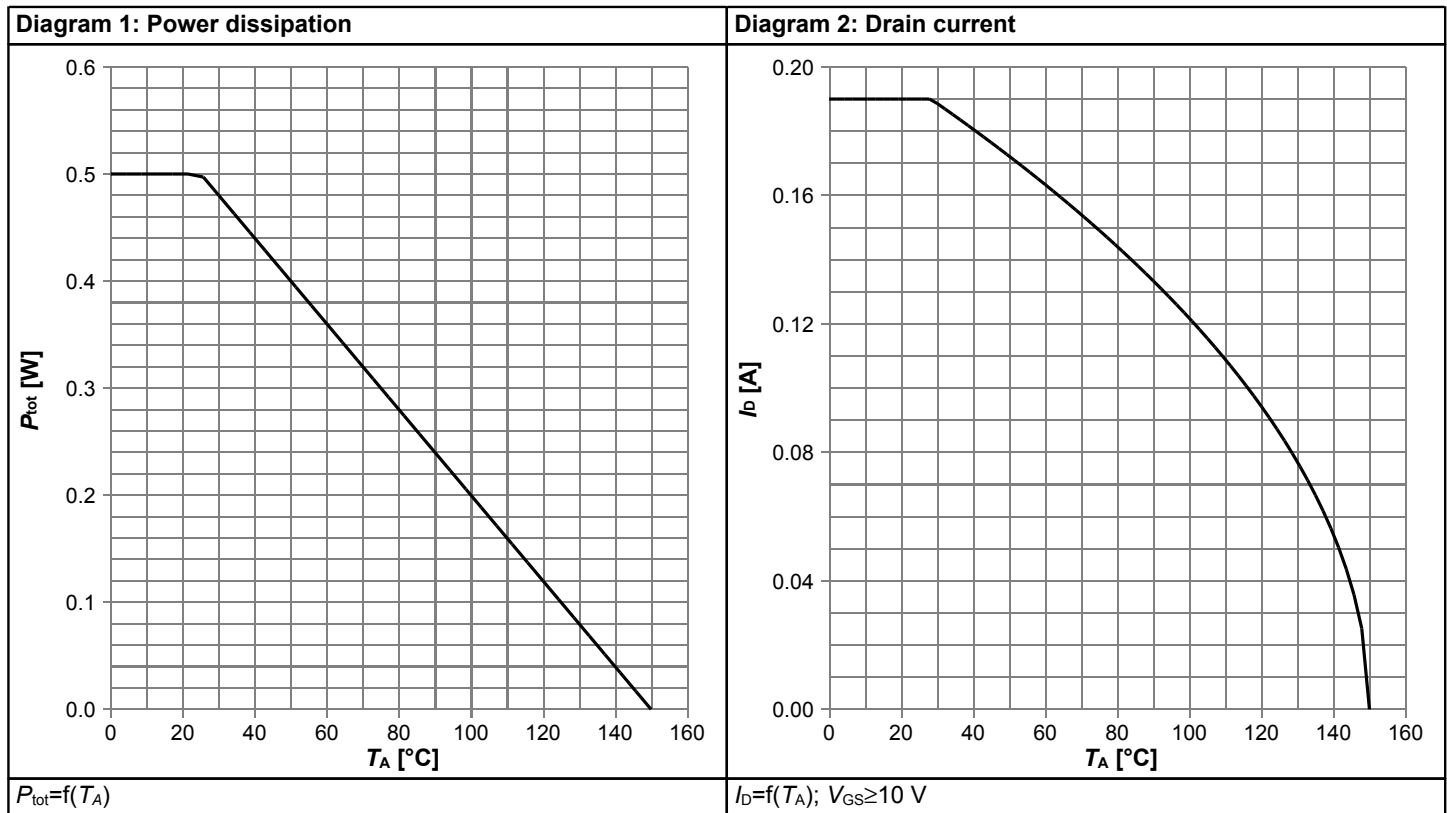
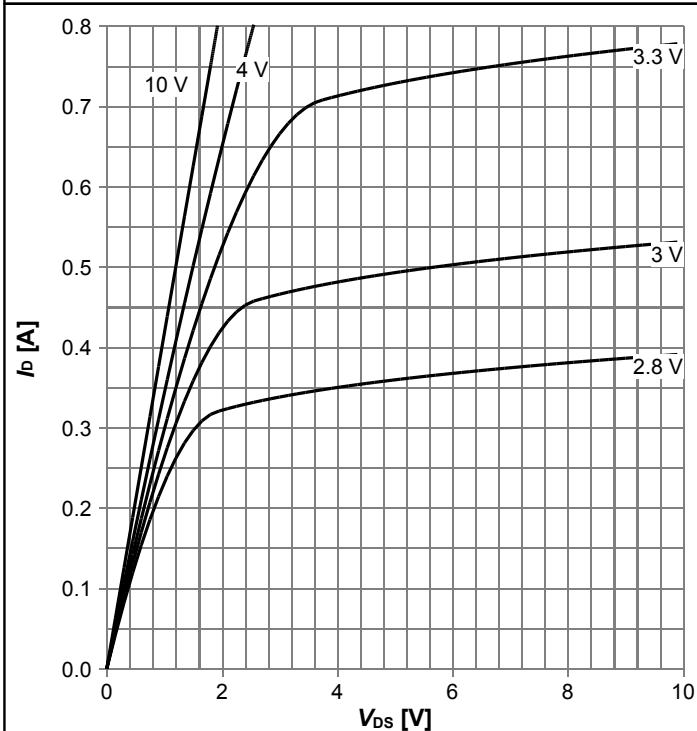
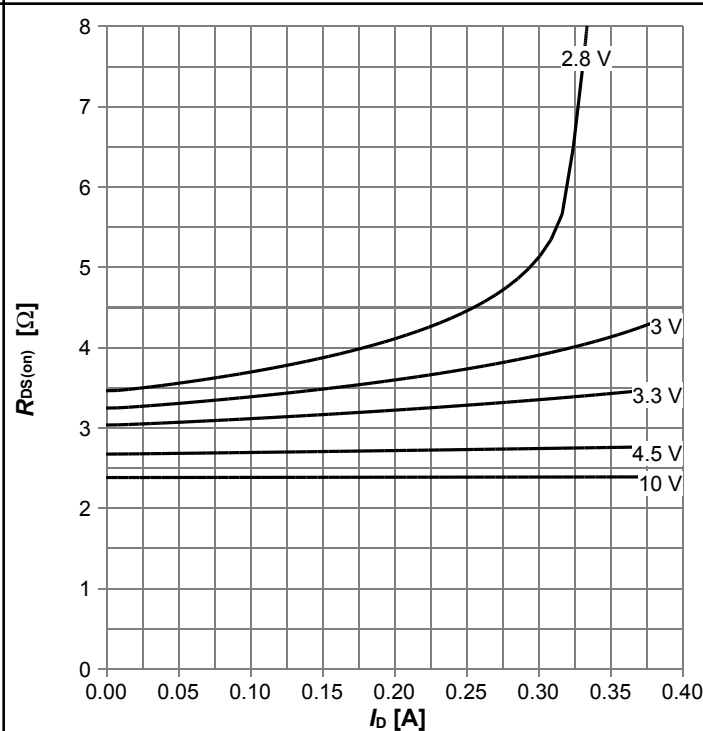


Diagram 5: Typ. output characteristics



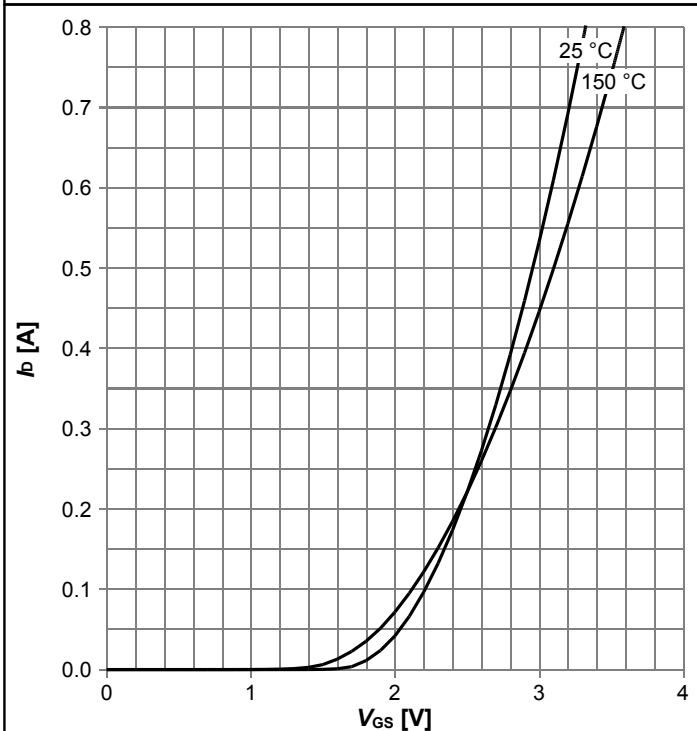
$I_D = f(V_{DS})$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



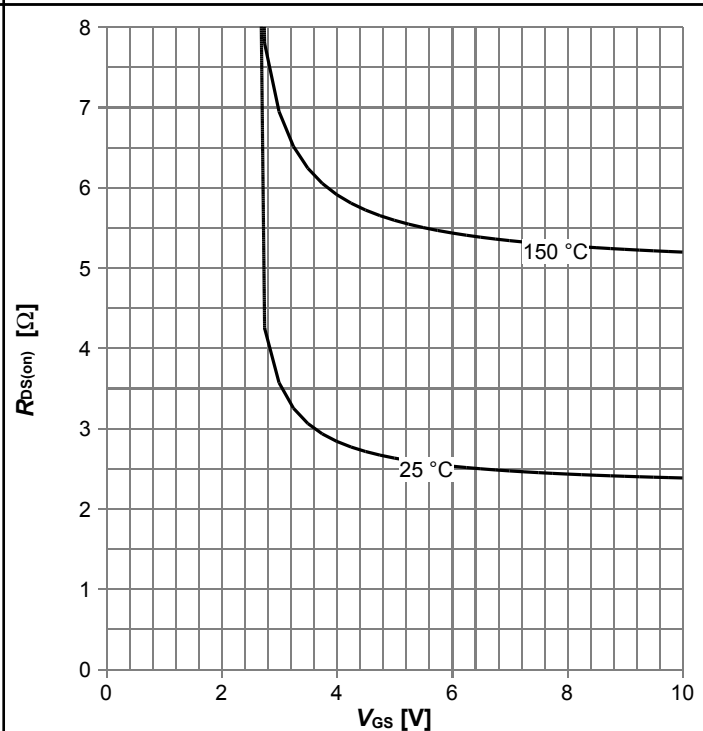
$R_{DS(on)} = f(I_D)$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



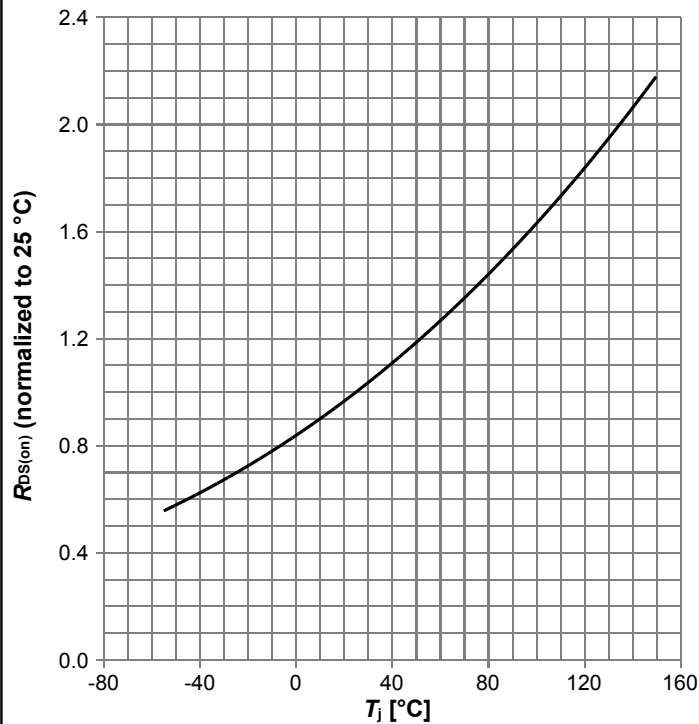
$I_D = f(V_{GS})$, $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



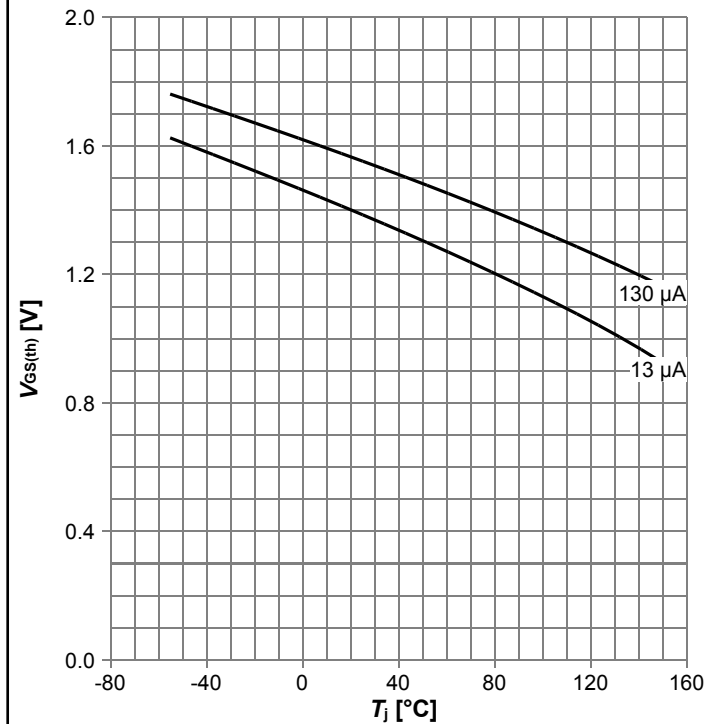
$R_{DS(on)} = f(V_{GS})$, $I_D = 0.19\text{ A}$; parameter: T_j

Diagram 9: Normalized drain-source on resistance



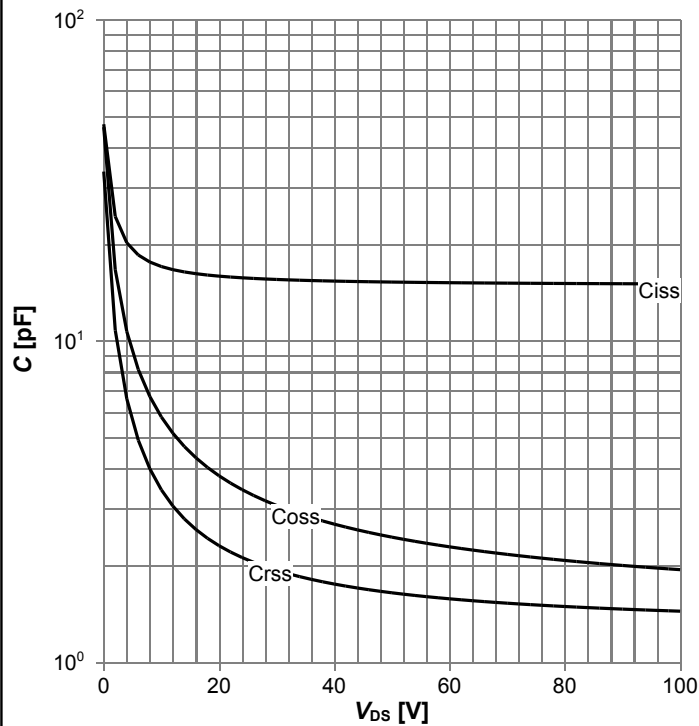
$R_{DS(on)} = f(T_j)$, $I_D = 0.19 \text{ A}$, $V_{GS} = 10 \text{ V}$

Diagram 10: Typ. gate threshold voltage



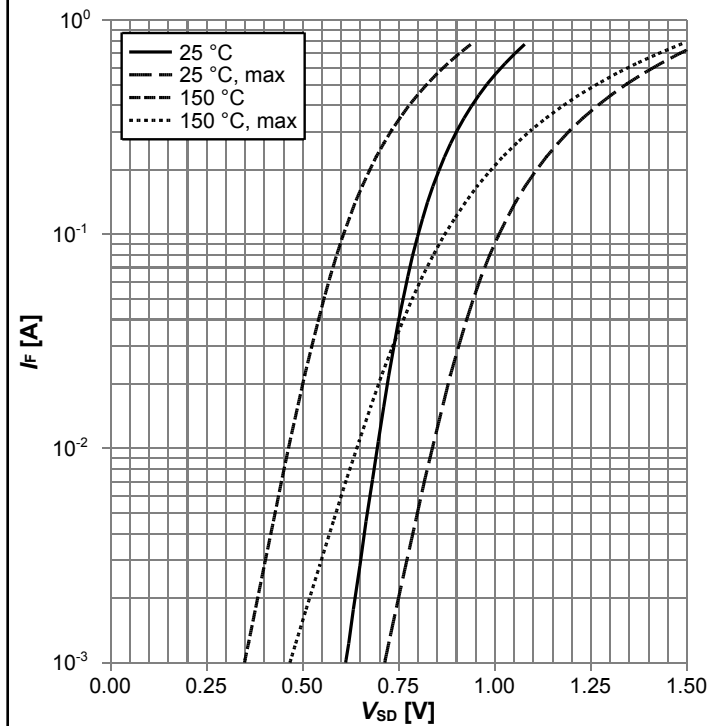
$V_{GS(th)} = f(T_j)$, $V_{GS} = V_{DS}$; parameter: I_D

Diagram 11: Typ. capacitances



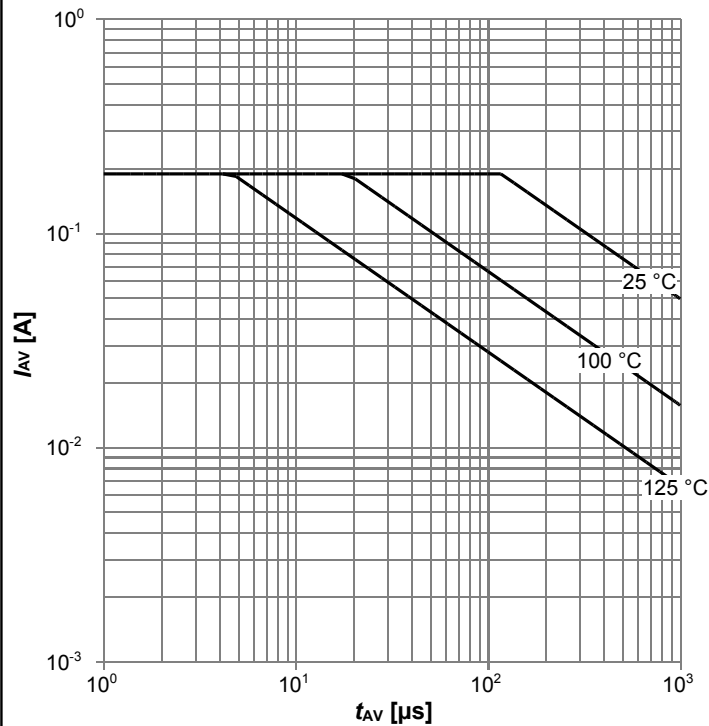
$C = f(V_{DS})$; $V_{GS} = 0 \text{ V}$; $f = 1 \text{ MHz}$

Diagram 12: Forward characteristics of reverse diode



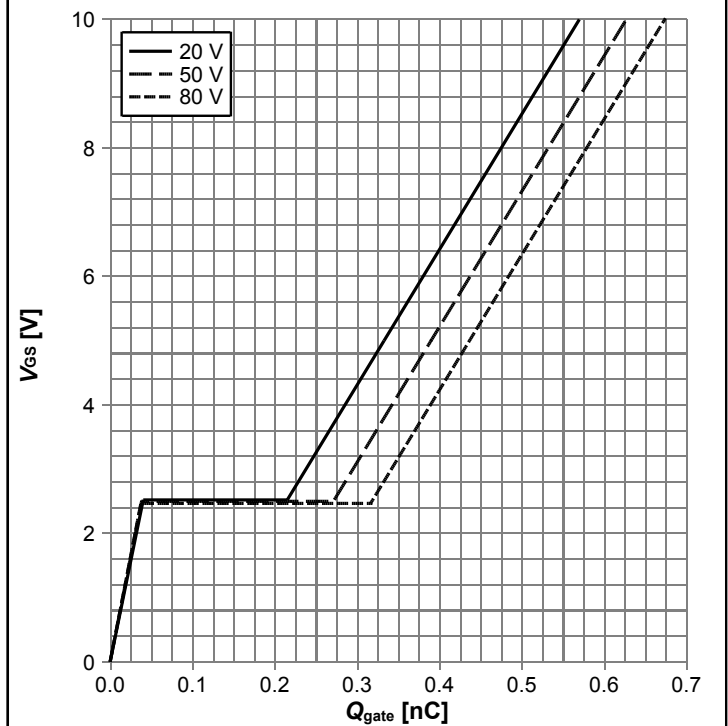
$I_F = f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



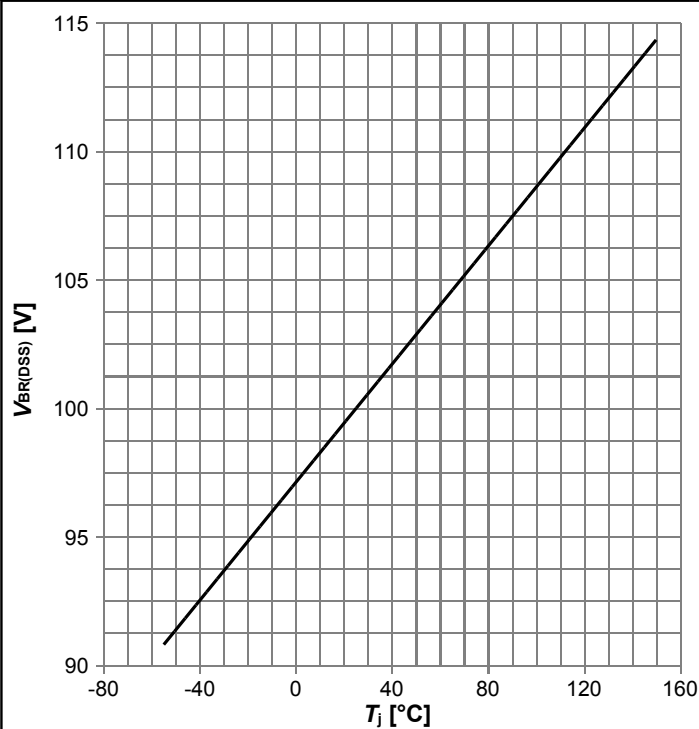
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



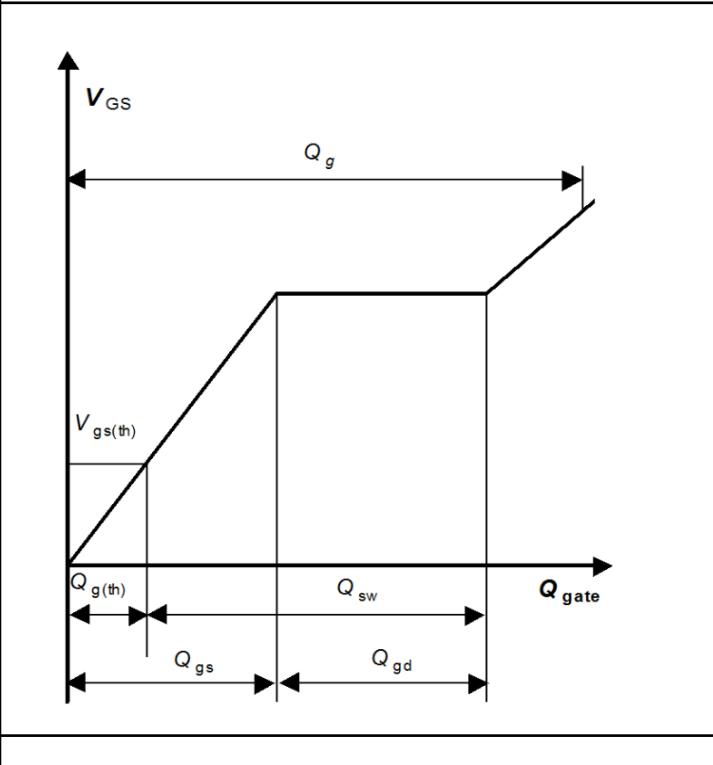
$V_{GS}=f(Q_{gate})$, $I_D=0.19\text{ A}$ pulsed, $T_j=25\text{ °C}$; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

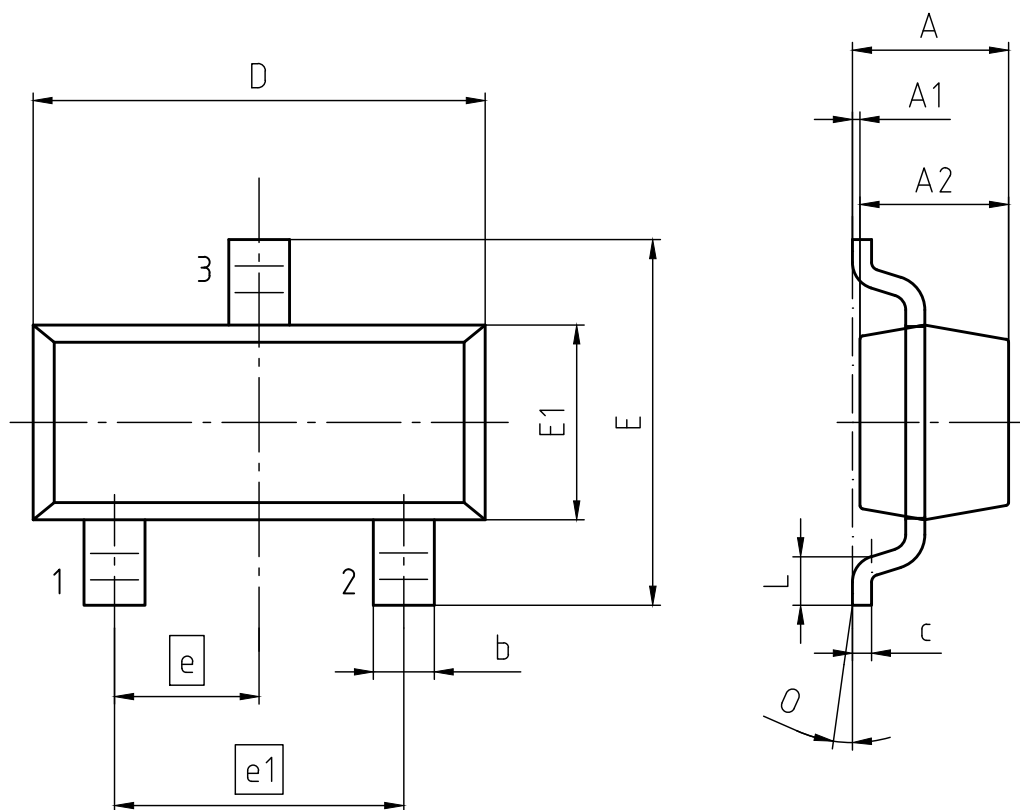


$V_{BR(DSS)}=f(T_j)$; $I_D=250\ \mu\text{A}$

Diagram Gate charge waveforms



5 Package Outlines



PACKAGE - GROUP NUMBER: PG-SOT23-3-U01		
REVISION: 01		DATE: 09.12.2020
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	0.89	1.12
A1	0.01	0.10
A2	0.88	1.02
b	0.30	0.50
c	0.08	0.20
D	2.80	3.04
E	2.10	2.64
E1	1.20	1.40
e	0.95	
e1	1.90	
L	0.15	0.60
O	0°	8°

Figure 1 Outline PG-SOT23, dimensions in mm

Revision History

BSS123I

Revision: 2021-02-01, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2021-01-26	Release of final version
2.1	2021-02-01	Update format

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